4. A method according to claim 1 wherein the printed circuit conductor pattern includes conductor regions less than about 30 microns wide.

5. A method according to claim 1 wherein the printed circuit conductor pattern includes conductor regions spaced by less than about 30 microns.

6. A method according to claim 1 wherein the etch band is less than about 30 microns wide.

7. A mask for use in producing a resist pattern for etching of a printed circuit, the mask being produced by the method of claim 1.

10. A printed circuit according to claim 8 wherein the etch band is of substantially the same width as the narrowest conductor or the narrowest separation between conductors in the printed circuit

11. A printed circuit according to claim 8wherein the printed circuit conductor pattern includes conductor regions less than about 30 microns wide.

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- 13. A printed circuit according to claim 8 wherein the etch band is less than 30 microns wide.
- 16. A method according to claim 14 wherein the pattern includes conductor elements spaced by less than about 30 microns.
- 17. A method according to claim 14 wherein the regions of constant width are of substantially the same width as the narrowest element or narrowest separation between elements in the printed circuit.